



## 25N65-CB

Preliminary

Power MOSFET

### 25A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

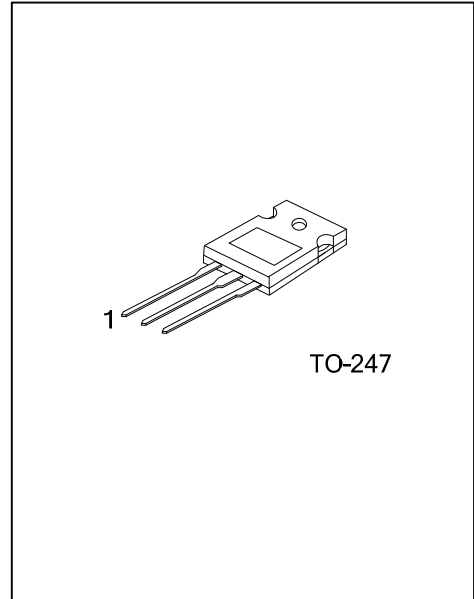
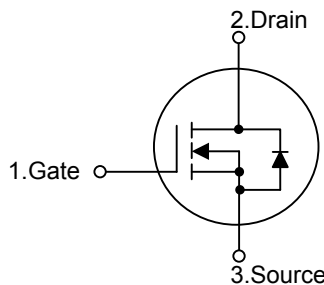
#### DESCRIPTION

The UTC **25N65-CB** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

#### FEATURES

- \*  $R_{DS(ON)} < 0.4\Omega @ V_{GS}=10V, I_D=12.5A$
- \* High Switching Speed
- \* 100% Avalanche Tested

#### SYMBOL



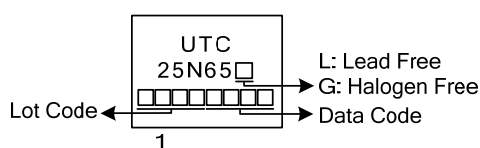
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
25N65L-T47-T	25N65G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>25N65L-T47-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) T47: TO-247</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	650	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	25	A
	Pulsed (Note 2)	$I_{DM}$	100	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	205	mJ
Peak Diode Recovery dv/dt		dv/dt	2	V/ns
Power Dissipation		$P_D$	367	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L = 10\text{mH}$ ,  $I_{AS} = 6.4\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 25\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	40	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{JC}$	0.34	$^\circ\text{C}/\text{W}$

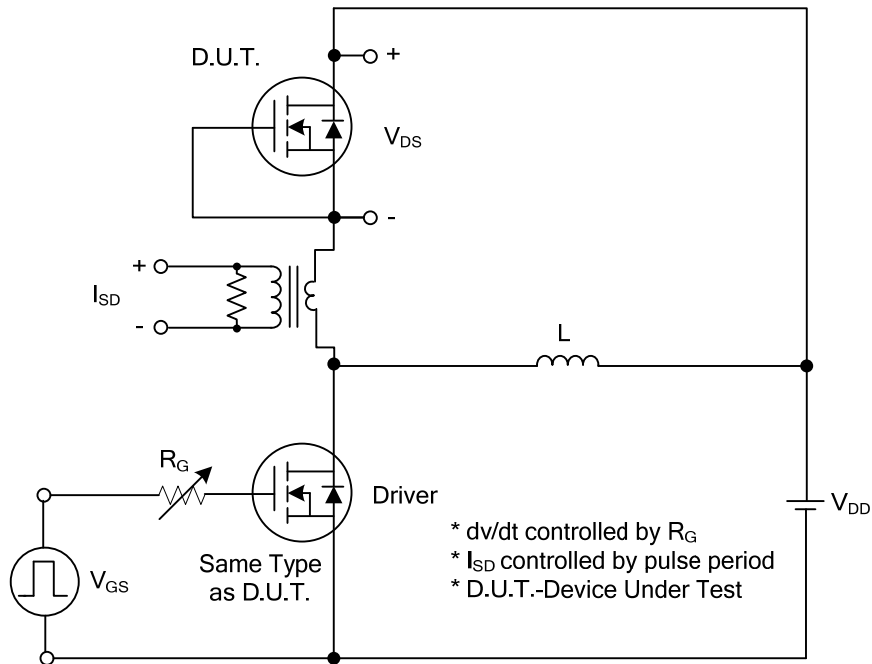
■ ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	650			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=650\text{V}$ , $V_{GS}=0\text{V}$			1	$\mu\text{A}$
Gate- Source Leakage Current	$I_{GSS}$	Forward			+100	nA
		Reverse	$V_{GS}=+30\text{V}$ , $V_{DS}=0\text{V}$			-100
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$ , $I_D=12.5\text{A}$			0.4	$\Omega$
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0\text{V}$ , $V_{DS}=10\text{V}$ , $f=1.0\text{MHz}$		4000		pF
Output Capacitance	$C_{OSS}$			1200		pF
Reverse Transfer Capacitance	$C_{RSS}$			15		pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge	$Q_G$	$V_{DS}=50\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=1.3\text{A}$ $I_G=100\mu\text{A}$ (Note1, 2)		274		nC
Gate to Source Charge	$Q_{GS}$			24		nC
Gate to Drain Charge	$Q_{GD}$			26		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DS}=30\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=0.5\text{A}$ , $R_G=25\Omega$ (Note1, 2)		152		ns
Rise Time	$t_R$			128		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			816		ns
Fall-Time	$t_F$			188		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	$I_S$				25	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				100	A
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S=25\text{A}$ , $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_S=25\text{A}$ , $V_{GS}=0\text{V}$		464		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$di/dt=100\text{A}/\mu\text{s}$ (Note 1)		7.4		$\mu\text{C}$

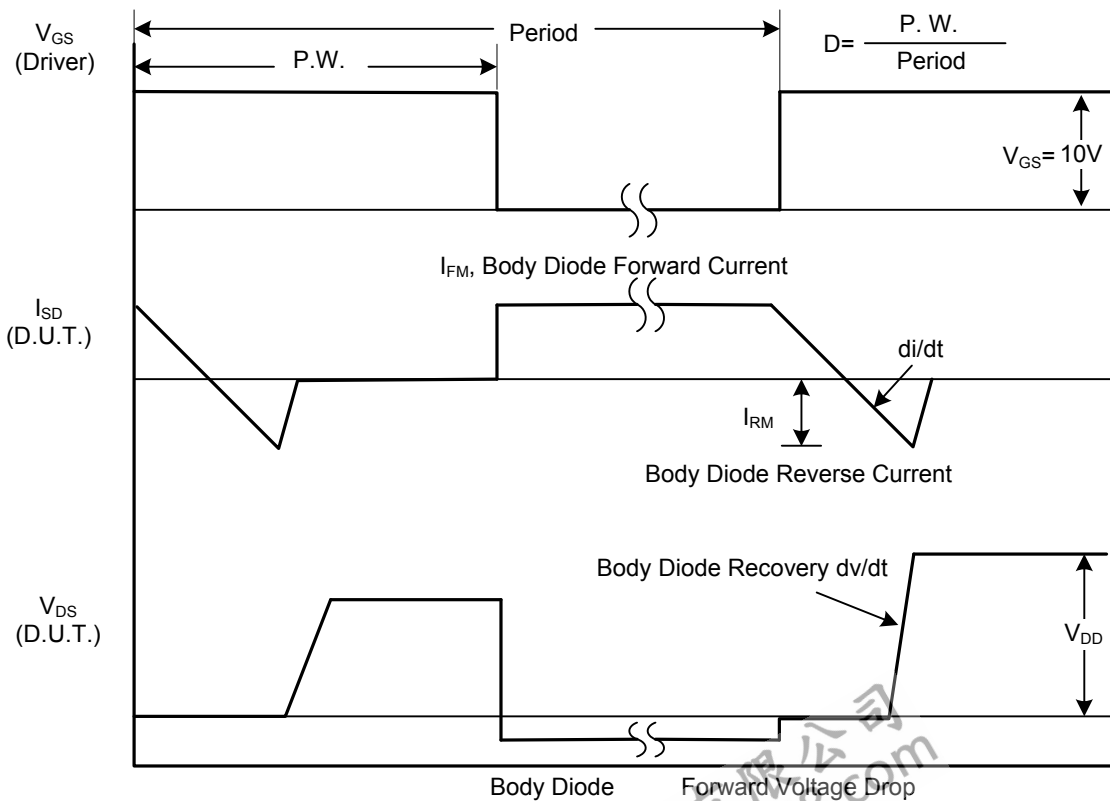
Notes: 1. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating ambient temperature.

TEST CIRCUITS AND WAVEFORMS



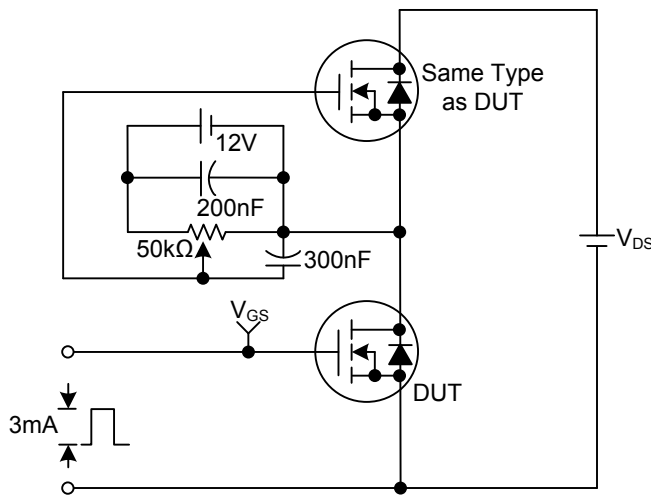
Peak Diode Recovery dv/dt Test Circuit



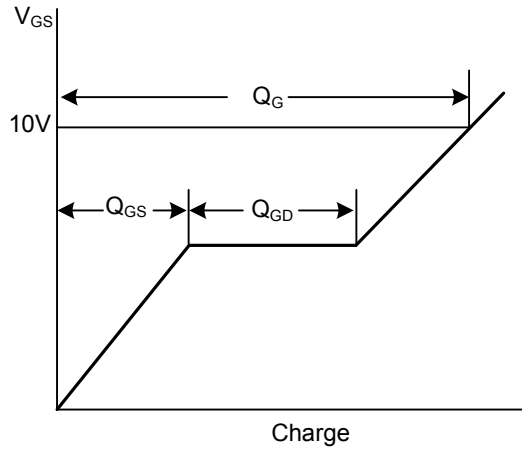
Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

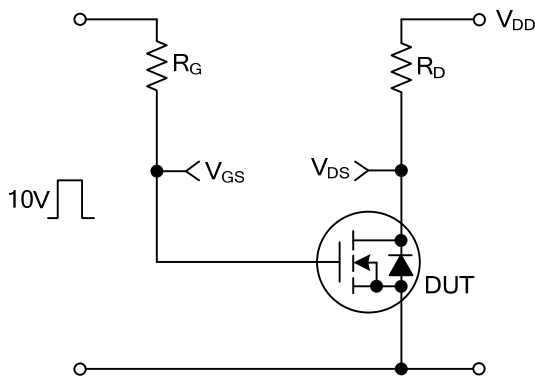
Gate Charge Test Circuit



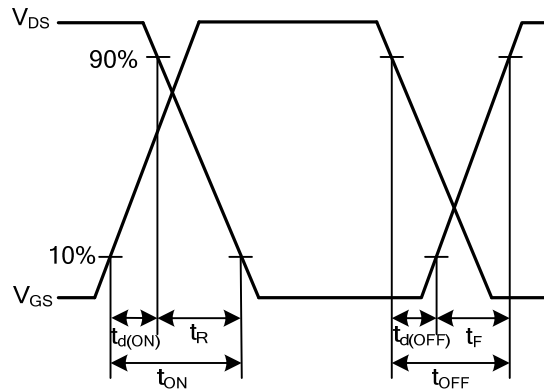
Gate Charge Waveforms



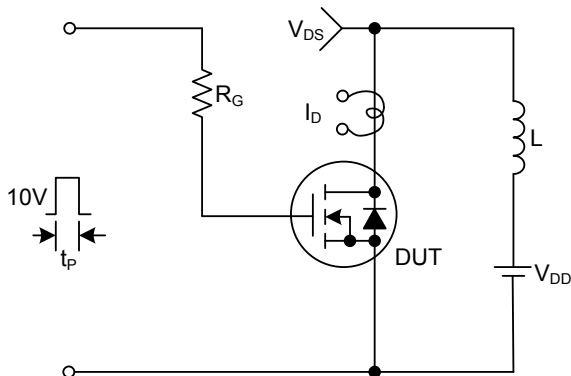
Resistive Switching Test Circuit



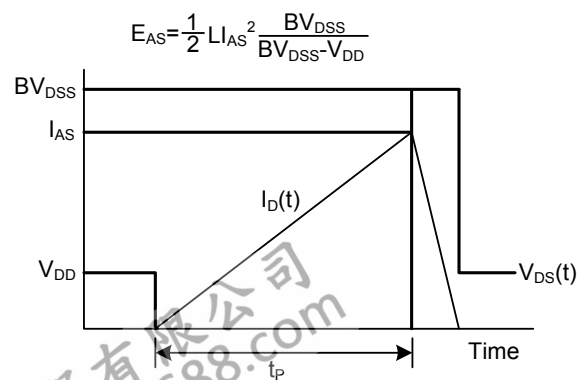
Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



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